

N-channel 80 V, 4.5 mΩ standard level MOSFET in D2PAK Rev. 1 — 22 March 2012 Product data of

Product data sheet

#### **Product profile** 1.

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#### **1.1 General description**

Standard level N-channel MOSFET in SOT404 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

#### **1.3 Applications**

- DC DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	80	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u>	[1]	-	-	100	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	306	W
Tj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
$R_{DSon}$	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; see <u>Figure 13</u> ; see <u>Figure 6</u>		-	6.27	7.4	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 6</u>		-	3.8	4.5	mΩ
Dynamic	characteristics						
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 40 V;		-	25	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 14; see Figure 15		-	125	-	nC
	e ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C};$ $I_D = 100 \text{ A}; \text{ V}_{sup} \le 80 \text{ V};$ $R_{GS} = 50 \Omega;$ unclamped		-	-	591	mJ
							-

[1] Continuous current is limited by package

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#### N-channel 80 V, 4.5 mΩ standard level MOSFET in D2PAK

#### **Pinning information** 2.

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D	drain	l	
				mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2

#### **Ordering information** 3.

#### Table 3. **Ordering information** Type number Package Name Description Version PSMN4R4-80BS D2PAK plastic single-ended surface-mounted package (D2PAK); 3 leads SOT404 (one lead cropped)

#### Marking 4.

Table 4. Mark	ng codes	
Type number	Ν	Marking code
PSMN4R4-80BS	F	PSMN4R4-80BS

#### N-channel 80 V, 4.5 mΩ standard level MOSFET in D2PAK

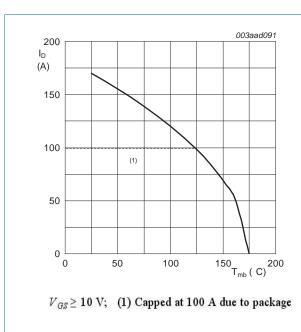
### 5. Limiting values

#### Table 5. Limiting values

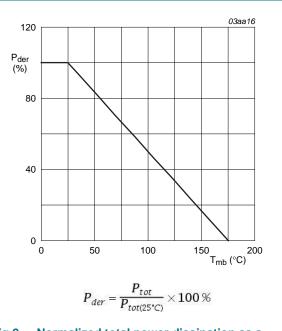
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	80	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	80	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	[1]	-	100	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	[1]	-	100	А
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 µs; T <sub>mb</sub> = 25 °C; see <u>Figure 3</u>		-	680	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	306	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-dra	ain diode					
ls	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	680	А
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$      V_{GS} = 10 \text{ V};  T_{j(init)} = 25 \text{ °C};  I_D = 100 \text{ A}; $		-	591	mJ

[1] Continuous current is limited by package



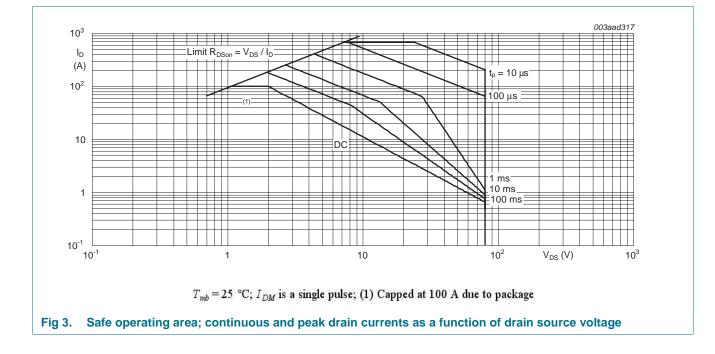
# Fig 1. Normalized continuous drain current as a function of mounting base temperature





# PSMN4R4-80BS

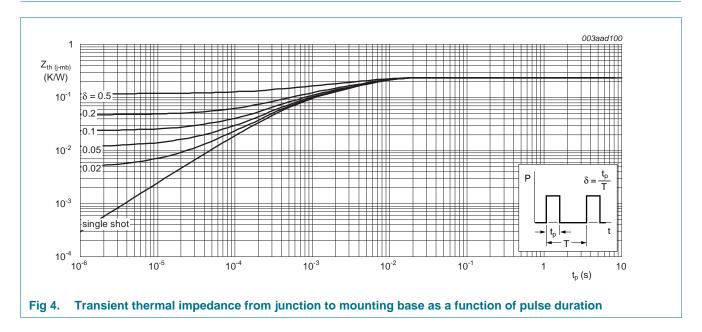
#### N-channel 80 V, 4.5 mΩ standard level MOSFET in D2PAK



#### N-channel 80 V, 4.5 m $\Omega$ standard level MOSFET in D2PAK

### 6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 4	-	0.23	0.49	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W



N-channel 80 V, 4.5 mΩ standard level MOSFET in D2PAK

### 7. Characteristics

#### Table 7. Characteristics

Tested to JEDEC standards where applicable.

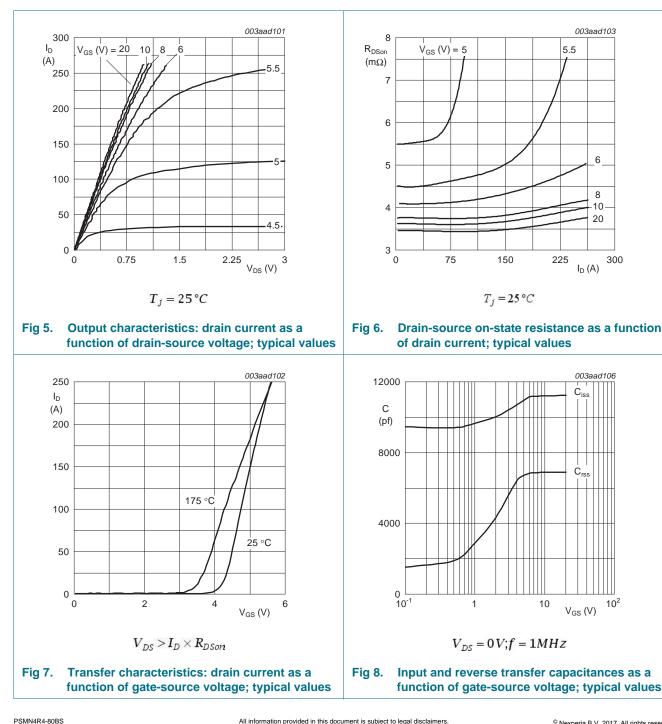
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	73	-	-	V
		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	80	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 11</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 11	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>	2	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 80 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.02	10	μA
		$V_{DS}$ = 80 V; $V_{GS}$ = 0 V; $T_j$ = 125 °C	-	-	200	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -20 \text{ V};  V_{DS} = 0   \text{V};  \text{T}_{j} = 25 ^{\circ}\text{C}$	-	10	100	nA
		$V_{GS} = 20 \text{ V};  V_{DS} = 0 \text{ V};  T_j = 25 ^{\circ}\text{C}$	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; \text{ I}_D = 25 \text{ A}; \text{ T}_j = 175 ^\circ\text{C};$ see <u>Figure 13</u> ; see <u>Figure 6</u>	-	9.12	10.7	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see Figure 13; see Figure 6	-	6.27	7.4	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 6</u>	-	3.8	4.5	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	1	-	Ω
Dynamic c	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}$	-	112	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	125	-	nC
$Q_{GS}$	gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	39	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	24	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	15	-	nC
$Q_{GD}$	gate-drain charge		-	25	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	4.65	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 40 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz};$	-	8400	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	700	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	336	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 40 \text{ V}; \text{ R}_{L} = 0.5 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	34.7	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 1.5 \Omega$	-	38.1	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	66	-	ns
t <sub>f</sub>	fall time		-	18.4	-	ns

#### N-channel 80 V, 4.5 mΩ standard level MOSFET in D2PAK

#### Characteristics ... continued Table 7.

Tested to JEDEC standards where applicable.

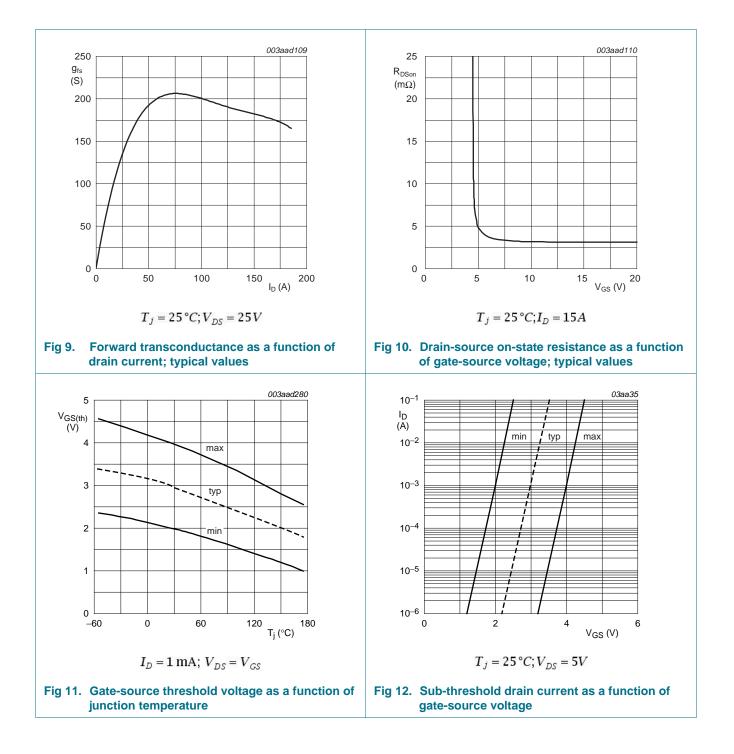
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dr	ain diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see Figure 17	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = 100 A/µs;	-	59	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 20 V$	-	130	-	nC



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# PSMN4R4-80BS

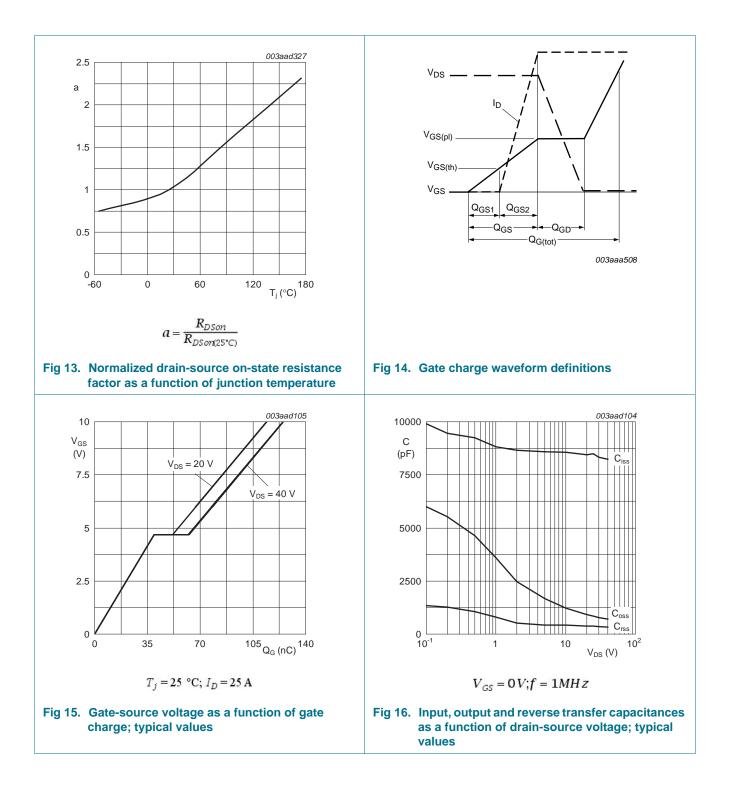
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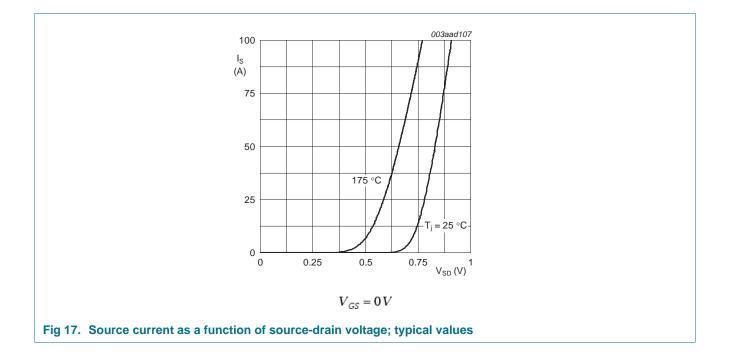
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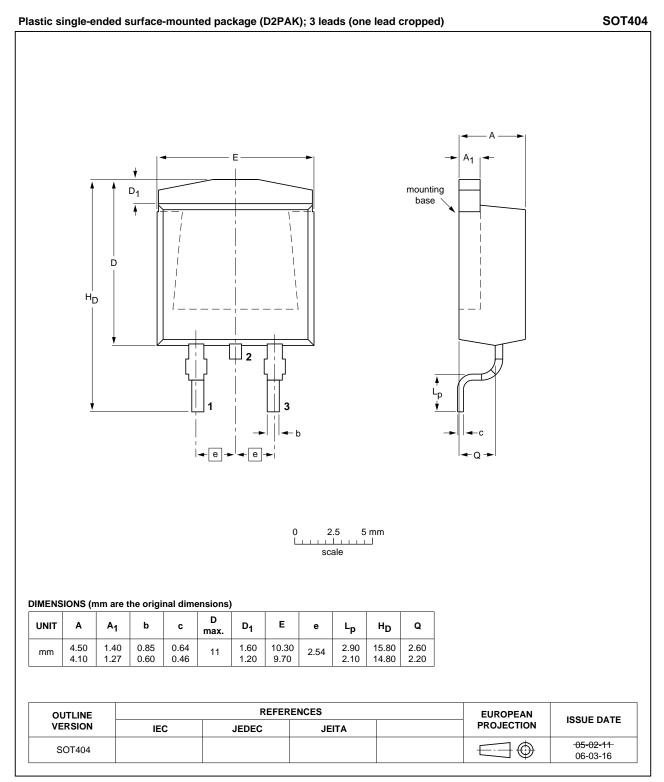
# PSMN4R4-80BS

#### N-channel 80 V, 4.5 m $\Omega$ standard level MOSFET in D2PAK



#### N-channel 80 V, 4.5 mΩ standard level MOSFET in D2PAK

### 8. Package outline



#### Fig 18. Package outline SOT404 (D2PAK)

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PSMN4R4-80BS

#### N-channel 80 V, 4.5 mΩ standard level MOSFET in D2PAK

### 9. Revision history

Table 8. Revision h	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PSMN4R4-80BS v.1	20120322	Product data sheet	-	-			

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Product data sheet

PSMN4R4-80BS

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